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6
Apêndice 1

A pesquisa conduzida durante este doutorado permitiu desenvolver um protótipo de sensor magnético utilizando o efeito OMAR. O protótipo consiste de um circuito analógico capaz de alimentar o dispositivo orgânico e coletar a variação da sua corrente na presença de campo magnético externo devido ao efeito magnetorresistência orgânica.

As figuras 6.1 e 6.2 apresentam o esquema elétrico e o desenho do circuito impresso, respectivamente, do protótipo. A figura 6.3 apresenta a foto do protótipo.

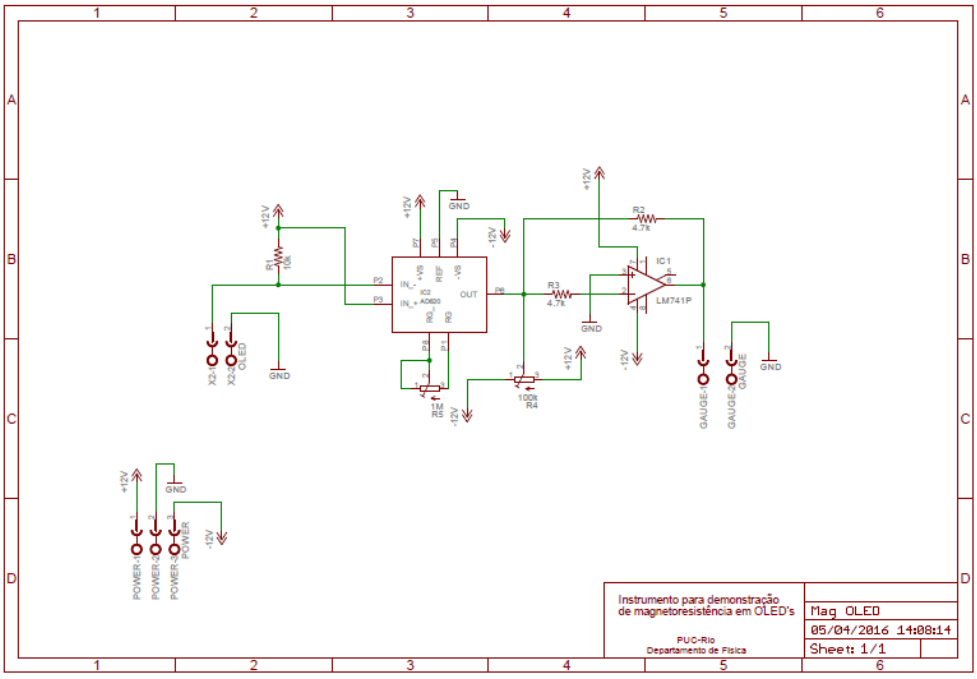

Figura 6.1 – Esquema elétrico do circuito utilizado no protótipo construído.

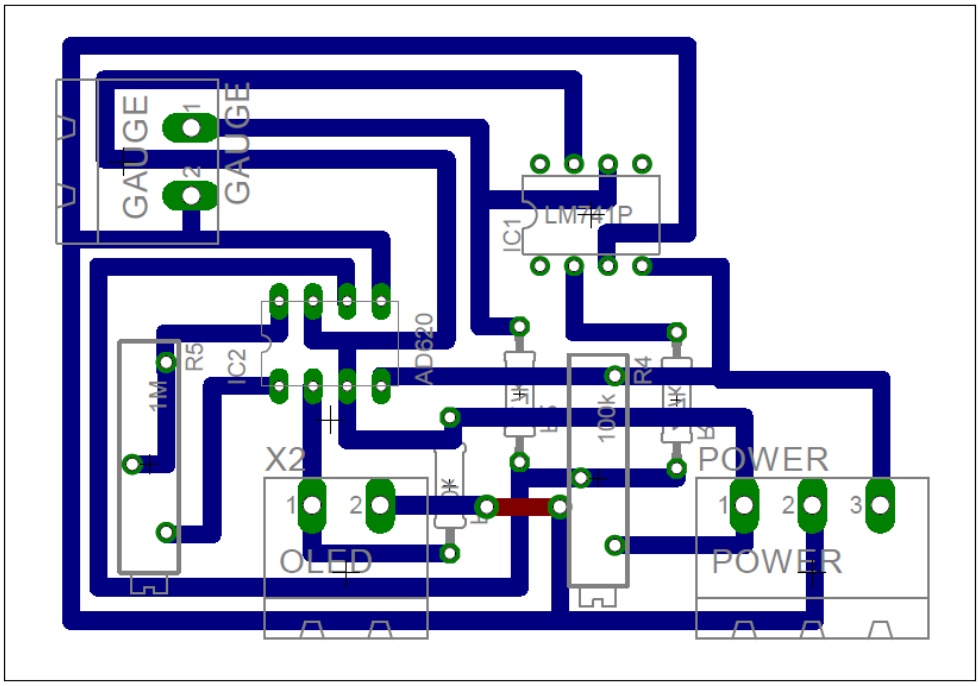

Figura 6.2 – Desenho do circuito impresso do protótipo de sensor de campo magnético desenvolvido.

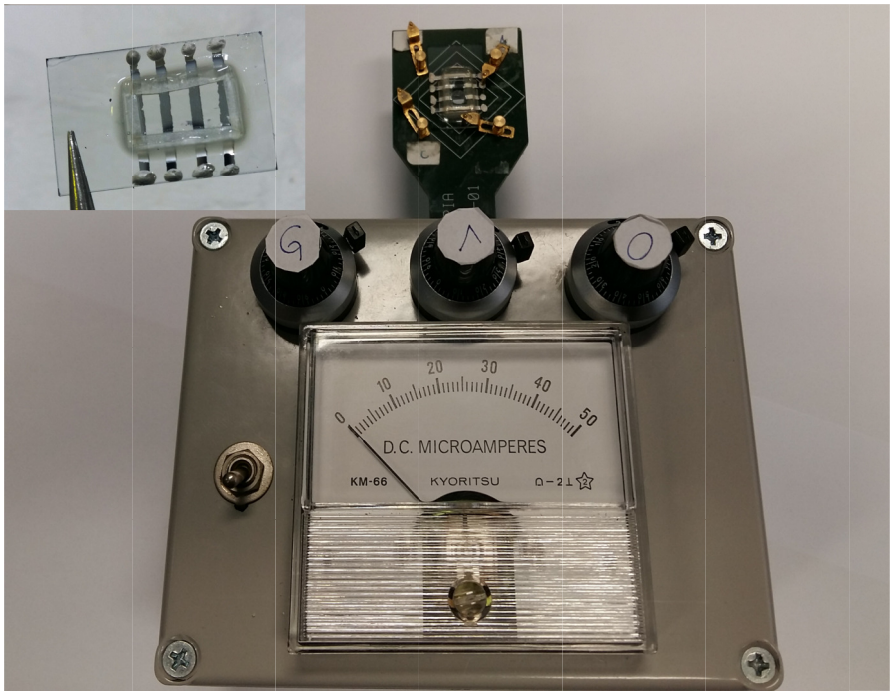

Figura 6.3 - Foto do circuito analógico do protótipo de sensor de campo magnético baseado no efeito de magnetorresistência orgânica.